Supporting Information

Enhanced Hole Injection in Phosphorescent Organic Light-Emitting Diodes by Thermally Evaporating a Thin Indium Trichloride Layer

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Figure S1. (a) The current density-voltage-luminance curves, (b) the current efficiency-current density curves, (c) the power efficiency-current density curves, and (d) the normalized EL spectra of Devices I, II, III, IV and V with the $InCl_3$ layer thicknesses of 0, 0.5, 1, 1.5 and 2 nm, respectively. Device III with 1 nm $InCl_3$ exhibits the best performance.

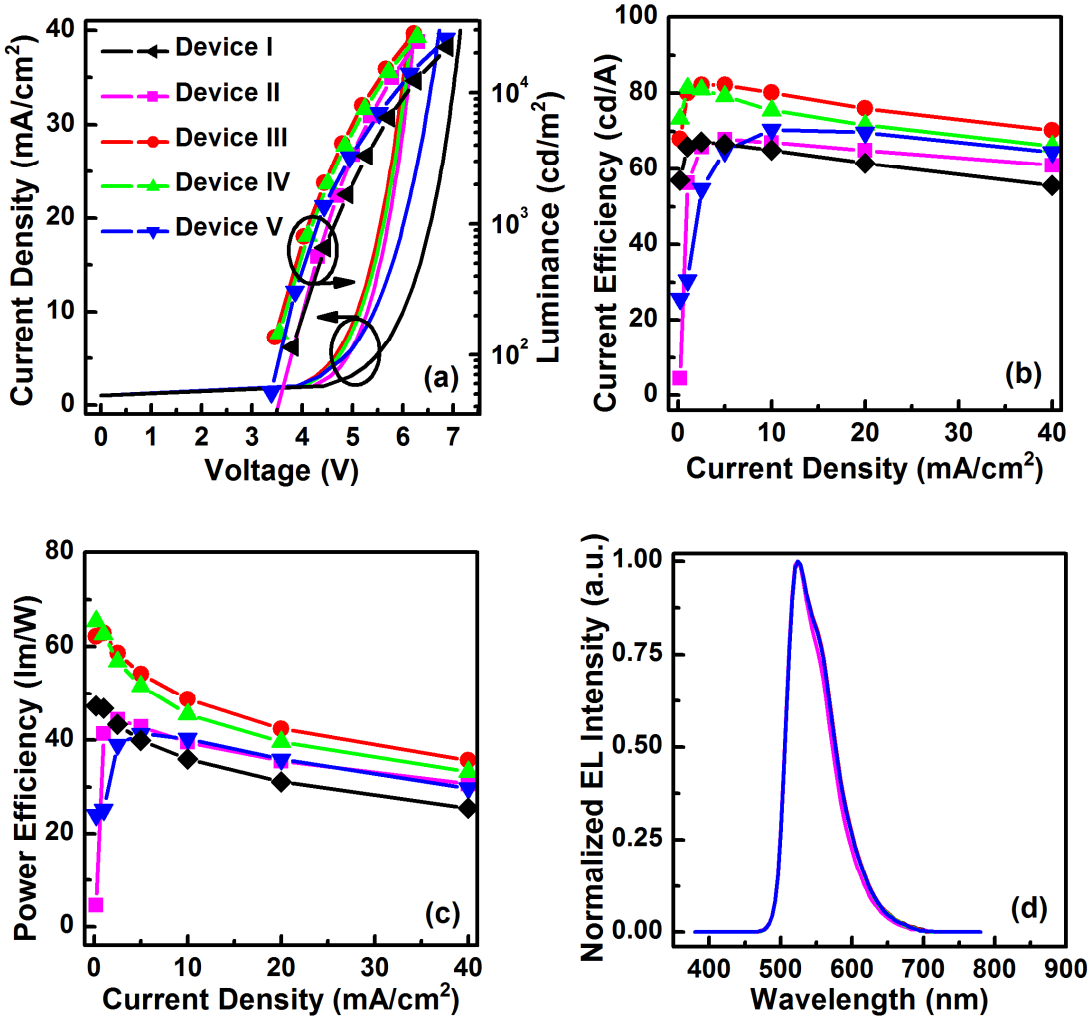


Figure S2. The log-log scale plot of current density-voltage curves of OLED Devices A, B and C. Device A: with 15 min UV-ozone treatment; Device B: with 15 min UV-ozone treatment and 1 nm thermally deposited $InCl_3$, and Device C with 1 nm CF_x deposited by plasma-assisted deposition of CHF_3.

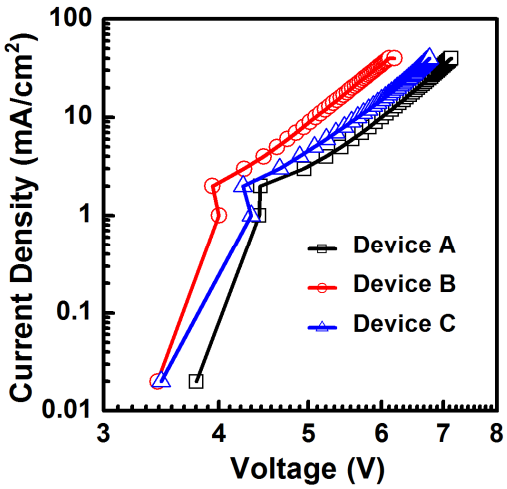
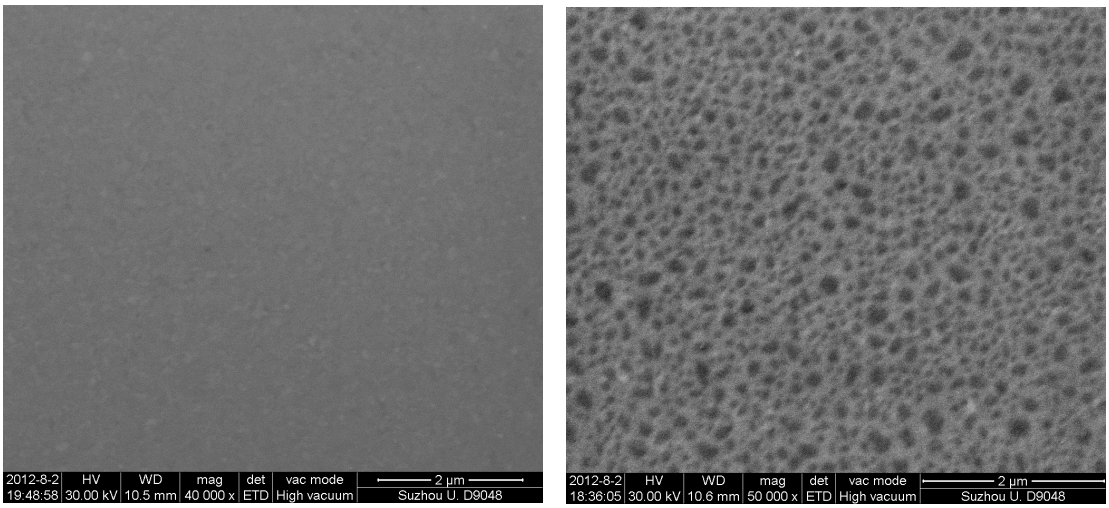


Figure S3. The SEM morphologies of (a) the ITO surface without $InCl_3$ and (b) with 1 nm $InCl_3$. The morphology of ITO surface with 1 nm $InCl_3$ is very different from that of the ITO without $InCl_3$.



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